

## High power NPN epitaxial planar bipolar transistor

### **Features**

- High breakdown voltage V<sub>CEO</sub> = 80 V
- Complementary to 2STW1693
- Typical f<sub>t</sub> = 20 MHz
- Fully characterized at 125 °C

## **Applications**

Audio power amplifier

### **Description**

The device is a NPN transistor manufactured in low voltage planar technology using base island layout. The resulting transistor shows good gain linearity coupled with low V<sub>CE(sat)</sub> behaviour. Recommended for 40 W to 70 W high fidelity audio frequency amplifier output stage.

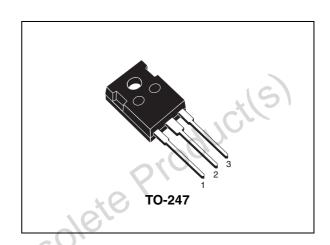


Figure 1. Internal schematic diagram

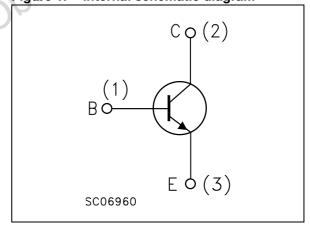


Table 1. Device summary

Order code	Marking	Package	Packaging
2STW4466	2STW4466	TO-247	Tube

2STW4466 Electrical ratings

#### **Electrical ratings** 1

Table 2. **Absolute maximum rating** 

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage (I <sub>E</sub> = 0)	100	V
$V_{CEO}$	Collector-emitter voltage (I <sub>B</sub> = 0)	80	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	6	V
I <sub>C</sub>	Collector current	6	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	12	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25 °C	60	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

Table 3.	Thermal data	, O,		
Symbol	Parameter	16/	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case	max	2.08	°C/W
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2STW4466 Electrical characteristics

#### **Electrical characteristics** 2

 $(T_{case} = 25^{\circ}C; unless otherwise specified)$ 

Table 4. **Electrical characteristics** 

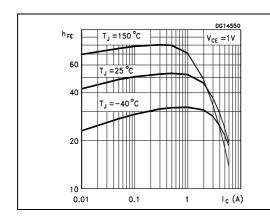
Symbol	Parameter	Test conditi	ons	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 100 V				0.1	μA
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6 V				0.1	μΑ
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA		6	. (	11/5	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100 μA		100	90		٧
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA		80			>
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	1	= 200 mA = 600 mA			0.6 1.5	V V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	V <sub>CE</sub> = 4 V I <sub>C</sub>	<sub>5</sub> = 6 A			1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 2 A$ V	<sub>CE</sub> = 4 V	50		120	
f <sub>T</sub>	Transition frequency	$I_C = 0.5 \text{ A}$ V	<sub>CE</sub> = 12 V		20		МН
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> = 0)	V <sub>CB</sub> = 10 V f	= 1 MHz		50		pF
	Resistive load						
t <sub>on</sub>	Turn-on time	$I_C = 3 A$ V	<sub>CC</sub> = 30 V		0.15		ns
t <sub>stg</sub>	Storage time	$I_{B1} = -I_{B2} = 0.3 A$			1.5		ns
t <sub>f</sub>	Fall time				0.1		ns

Electrical characteristics 2STW4466

# 2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. DC current gain



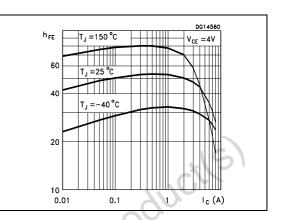
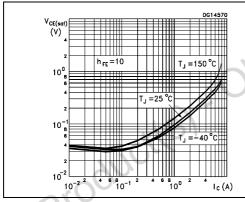


Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage



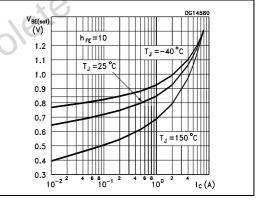
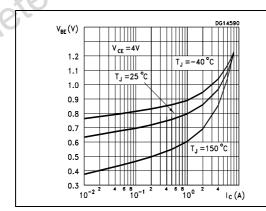
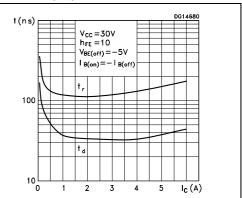


Figure 6. Base emitter voltage

Figure 7. Resistive load switching time (on)

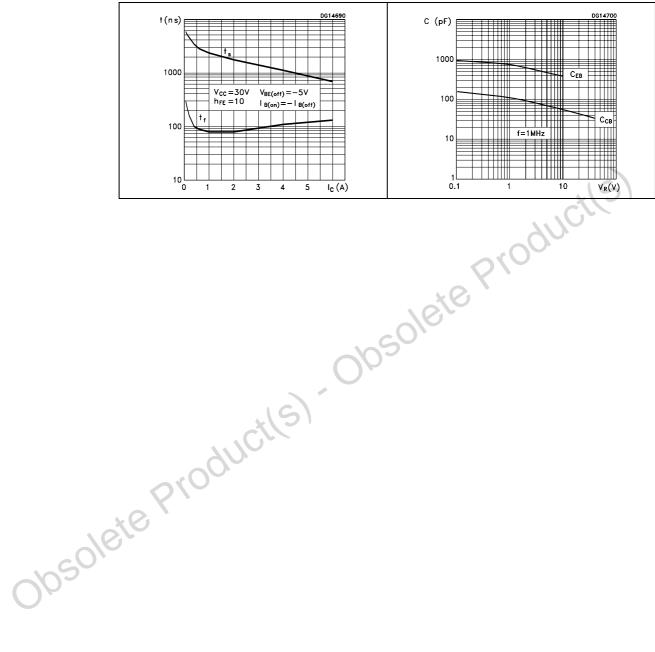




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2STW4466 Electrical characteristics

Figure 8. Resistive load switching time Figure 9. Emitter-base and collector-(off) base capacitance



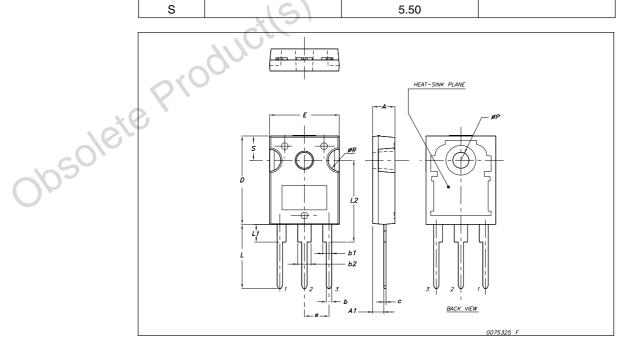
# 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s).

#### **TO-247 Mechanical data**

Dim.	mm.				
<b>D</b> iiii.	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
Е	15.45		15.75		
е		5.45			
L	14.20	7/6,	14.80		
L1	3.70	60,	4.30		
L2		18.50			
øΡ	3.55		3.65		
øR	4.50		5.50		
S	16	5.50			



Revision history 2STW4466

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes	
11-Oct-2007	1	First release	
25-Sep-2008	2	Content reworked to improve readability, no technical changes.	

Obsolete Product(s). Obsolete Product(s)

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